

**IN THE CLAIMS:**

Please AMEND claims 1 and 11 and ADD new claim 12 in accordance with the following:

1. (CURRENTLY AMENDED) A display device with a polysilicon substrate, comprising:
  - a display region;
  - a driving region;
  - a first plurality of thin film transistors in the display region;
  - a second plurality of thin film transistors in the driving region;~~and~~
  - primary crystal grain boundaries in the polysilicon substrate in the display region and in the driving region;
  - secondary crystal grain boundaries in the polysilicon substrate in the display region and in the driving region;
  - wherein the primary crystal grain boundaries are inclined to a first direction of current flowing from source to drain of each of the first plurality of thin film transistors at an angle of -30° to 30° and the secondary crystal grain boundaries are inclined to a second direction of current flowing from source to drain of each of the first plurality of thin film transistors, and
  - wherein the primary crystal grain boundaries are inclined to athe second direction of current flowing from source to drain of each of the second plurality of thin film transistors at an angle of 30° to 150° and the secondary crystal grain boundaries are inclined to the first direction of the current flowing from source to drain of each of the second plurality of thin film transistors.
2. (ORIGINAL) The display device according to claim 1, wherein the primary crystal grain boundaries are parallel to the first direction of current.
3. (ORIGINAL) The display device according to claim 2, wherein a first number of the primary crystal grain boundaries exist in active channel regions of each of the first plurality of thin film transistors.
4. (ORIGINAL) The display device according to claim 1, wherein the display device is an organic electroluminescent display device.
5. (ORIGINAL) The display device according to claim 1, wherein the polysilicon substrate is fabricated by an SLS (sequential lateral solidification) method.

6. (CANCELLED)

7. (PREVIOUSLY PRESENTED) The display device according to claim 1, wherein the primary crystal grain boundaries are perpendicular to the second direction of current.

8. (ORIGINAL) The display device according to claim 7, wherein a second number of the primary crystal grain boundaries exist in active channel regions of each of the second plurality of thin film transistors.

9. (CANCELLED)

10. (CANCELLED)

11. (CURRENTLY AMENDED) A display device with a polysilicon substrate comprising:  
a driving region;  
a plurality of thin film transistors in the driving region;  
primary crystal grain boundaries in the polysilicon substrate in the driving region; and  
secondary crystal grain boundaries in the polysilicon substrate in the driving region;  
wherein the primary crystal grain boundaries are inclined to a direction of current flowing from source to drain of each of the plurality of thin film transistors at an angle of 30° to 150° and the secondary crystal grain boundaries are substantially ~~perpendicular~~parallel to the current flowing from the source to the drain.

12. (NEW) A display device with a polysilicon substrate comprising:  
a display region;  
a plurality of thin film transistors in the display region;  
primary crystal grain boundaries in the polysilicon substrate in the display region; and  
secondary crystal grain boundaries in the polysilicon substrate in the display region;  
wherein the primary crystal grain boundaries are inclined to a direction of current flowing from source to drain of each of the plurality of thin film transistors at an angle of -30° to 30° and the secondary crystal grain boundaries are substantially perpendicular to the current flowing from the source to the drain.